

Abstract of the Disclosure

[0042] A multi-point calibration standards and a method of fabricating calibration standards which are used to quantify the dose or concentration of a dopant or impurity in a silicon matrix. The calibration standards include a set of calibration standard wafers for each dopant or impurity to be quantified. On each calibration standard wafer in the set is provided a silicon matrix incorporated with one of various concentrations, by weight, of the dopant or impurity in the silicon. The atomic concentration of the dopant or impurity in the silicon on each wafer in the set is measured. A calibration curve is then prepared in which the silicon/dopant or silicon/impurity ratio on each calibration standard wafer in the set is plotted versus the atomic concentration of the dopant or impurity in the silicon on the wafer.